Weebit Nano successfully scales up to 4Kb array 40nm working cells

On track to achieve 40nm 1Mb array by mid-2018

8 Feb, 2018 – Weebit Nano (ASX: WBT), the Israel-based semiconductor company seeking to develop and commercialise the next generation of memory technology is pleased to report successful characterisation results on its first 4Kb array wafers on 40nm memory size, which demonstrated a capability of more than 99 per cent working cells inside an array, similar to that of flash memories currently in production.

Following the previous announcement on 27 November 2017 where Weebit Nano demonstrated a 40nm working memory cell one month ahead of schedule, the Company has successfully scaled up the single memory cell into a 4Kb array (an array with more than 4,000 cells). Analysis of the 4Kb wafers showed no degradation due to scaling, and provides Weebit Nano with a great deal of confidence as it works towards its stated goal of a working 40nm 1Mb array (an array with more than 1 million cells) by mid-2018.

Commenting on the excellent results, **Coby Hanoch, CEO of Weebit Nano**, said: "We are very encouraged with the results our dedicated team have achieved, which demonstrates that our next generation memory technology is scalable. Having achieved the 40nm working cell, the next challenge was to build memory arrays of multiple cells. The 4Kb results show that our technology can scale up its capacity, and we now look forward to achieving the 1Mb array milestone by mid-2018.

"These results are further testament of how the benefits of Weebit Nano's unique silicon oxide technology, in combination with a talented team of scientists and a strong partner in Leti, has enabled technology development at a rapid pace and at a substantially lower cost. We have achieved more in under two years than other companies have managed in up to ten, and we believe this speed to market is a significant competitive advantage for us. Our team is now laying out plans for memory integration at more advanced scalable technology nodes", said Mr Hanoch.

The 4Kb experiments were performed using smart programming techniques that verified appropriate stress levels to each memory cell. The data analysed from this experiment was used to launch the next set of experimental wafers, which are now running in Leti's cleanroom fab. These wafers have been scaled up the 1Mb capacity, and the aim is to achieve working cells by mid-2018. In addition, experiment conditions will be further narrowed to facilitate further technology optimisation.

The Company will continue to provide updates as progress is achieved.

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About Weebit Nano Limited

Weebit Nano is a leader in the development of next generation computer memory storage, and plans to become the new industry standard in this space. Its goal is to address the growing need for a significantly higher performance and lower power data storage technology. Weebit Nano's ReRAM technology is based on fab-friendly Silicon Oxide, allowing the company to rapidly execute, without the need for special equipment or preparations. The company secured several patents to ensure optimal commercial and legal protection for its ground-breaking technology.

Weebit Nano's technology enables a quantum leap, allowing semiconductor memory elements to be significantly cheaper, faster, more reliable and more energy efficient than the existing Flash technology. Weebit Nano has signed an R&D agreement with Leti, an R&D institute that specialises in nanotechnologies, to further develop SiOx ReRAM technology.

For more information please visit: http://www.weebit-nano.com/